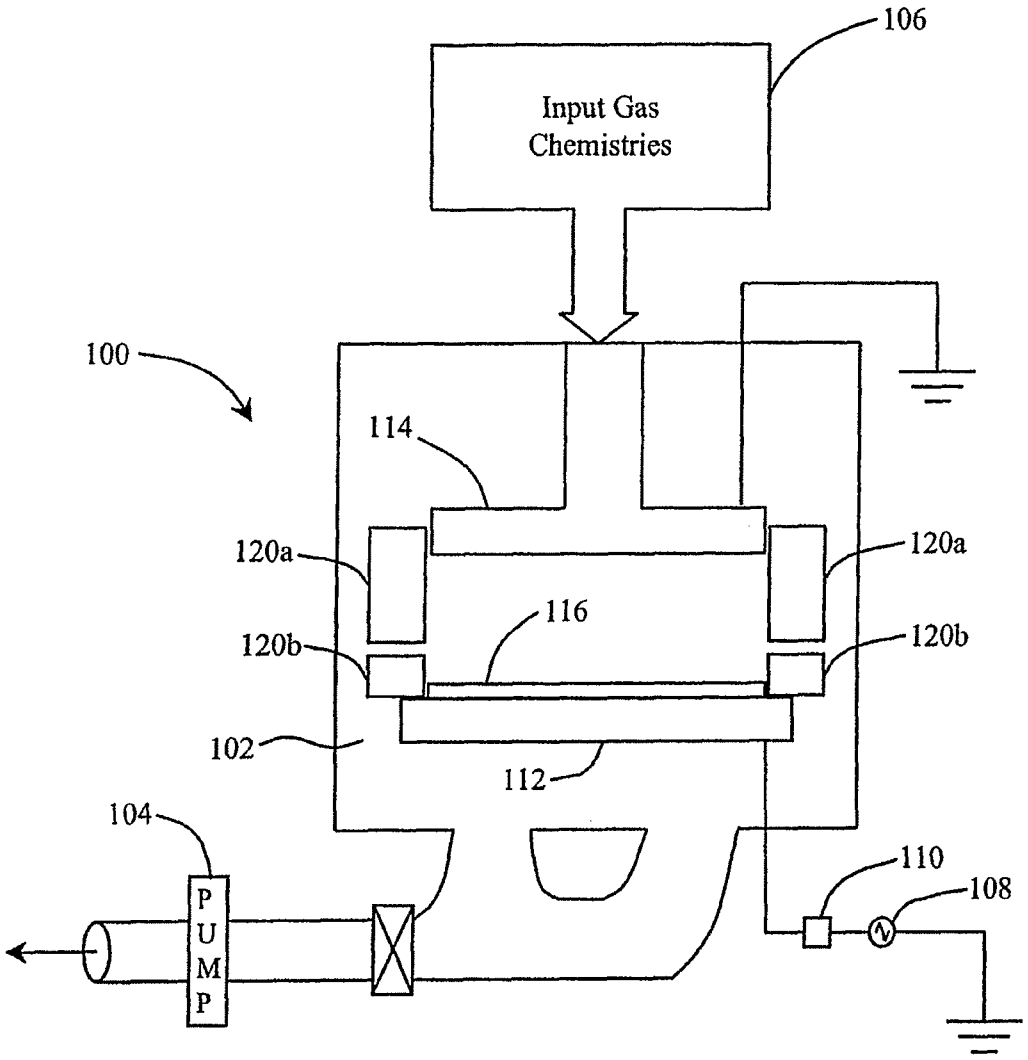

106
Input Gas
Chemistries
100
114
120a
120a
116
120b
120b
102
112
104
110
108
P
U
M
P

FIG. 1

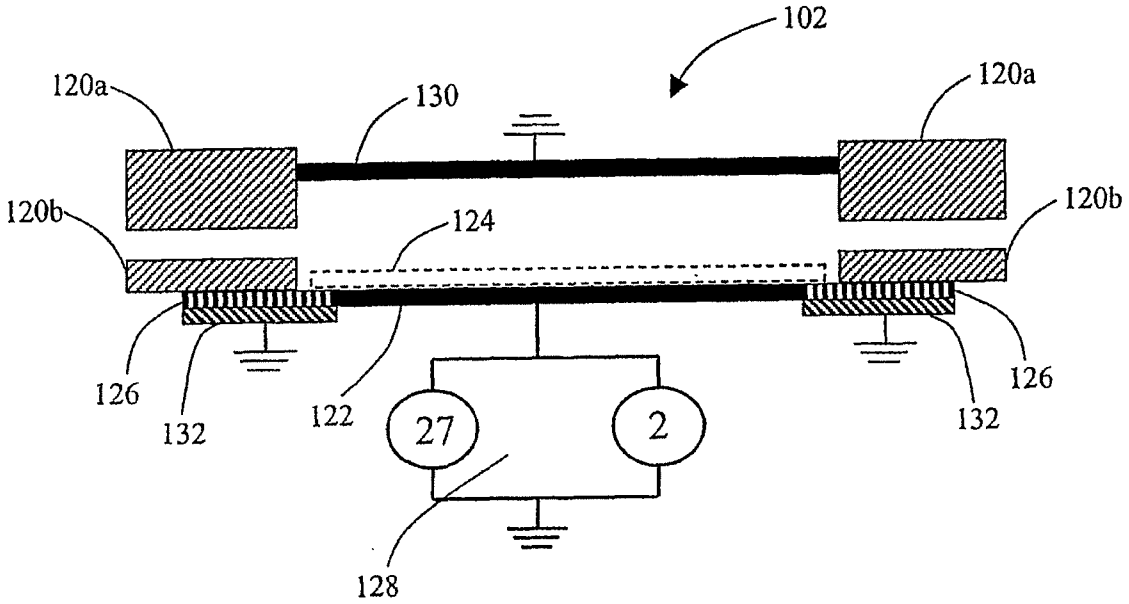


FIG. 2
(Prior Art)

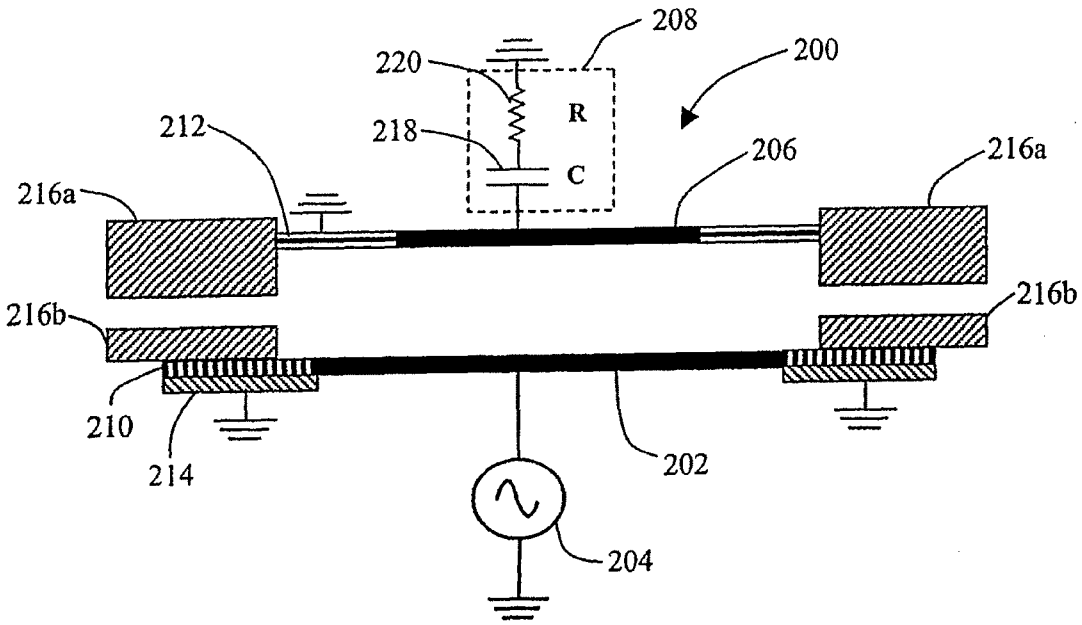


FIG. 3

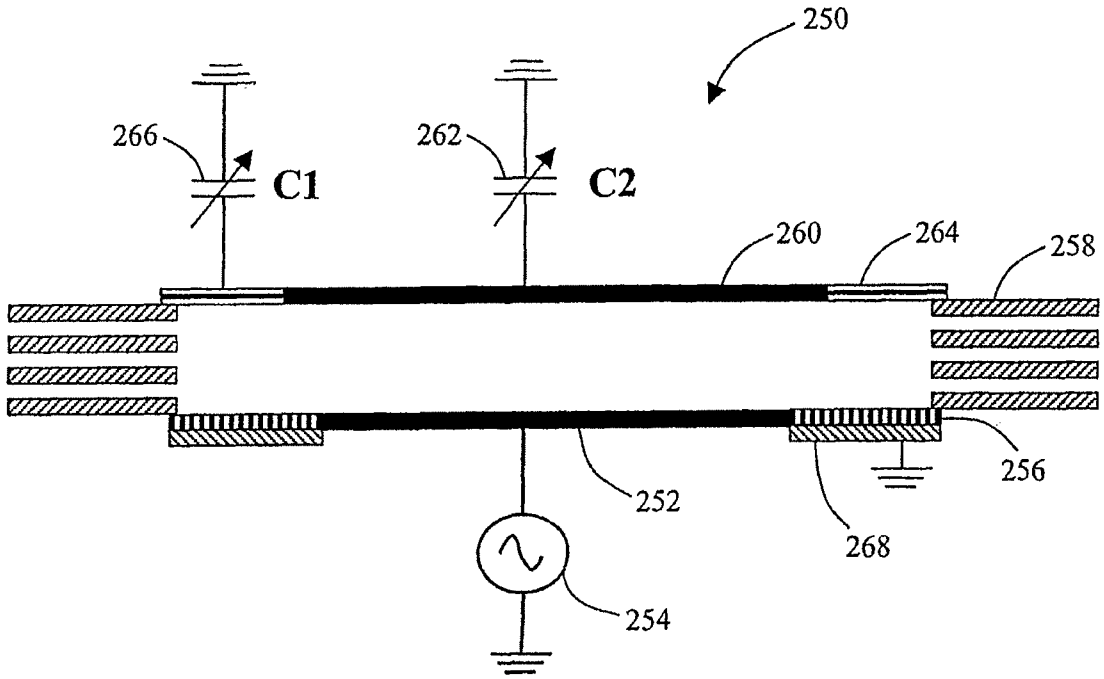

250
266
C1
262
C2
260
264
258
256
252
268
254

FIG. 4

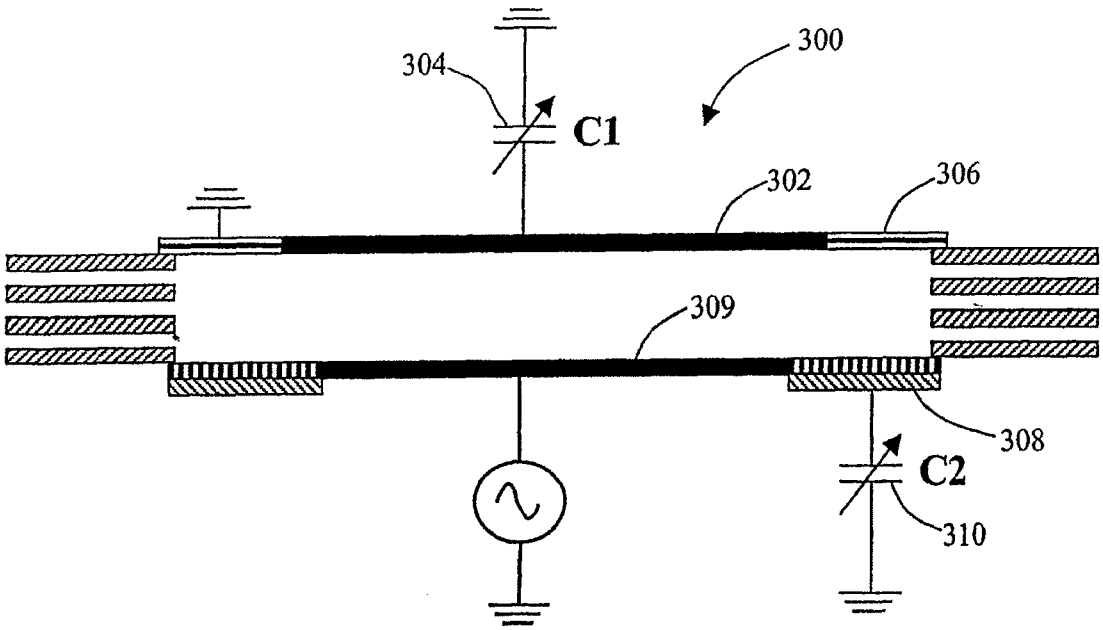

304
C1
300
302
306
309
308
C2
310

FIG. 5

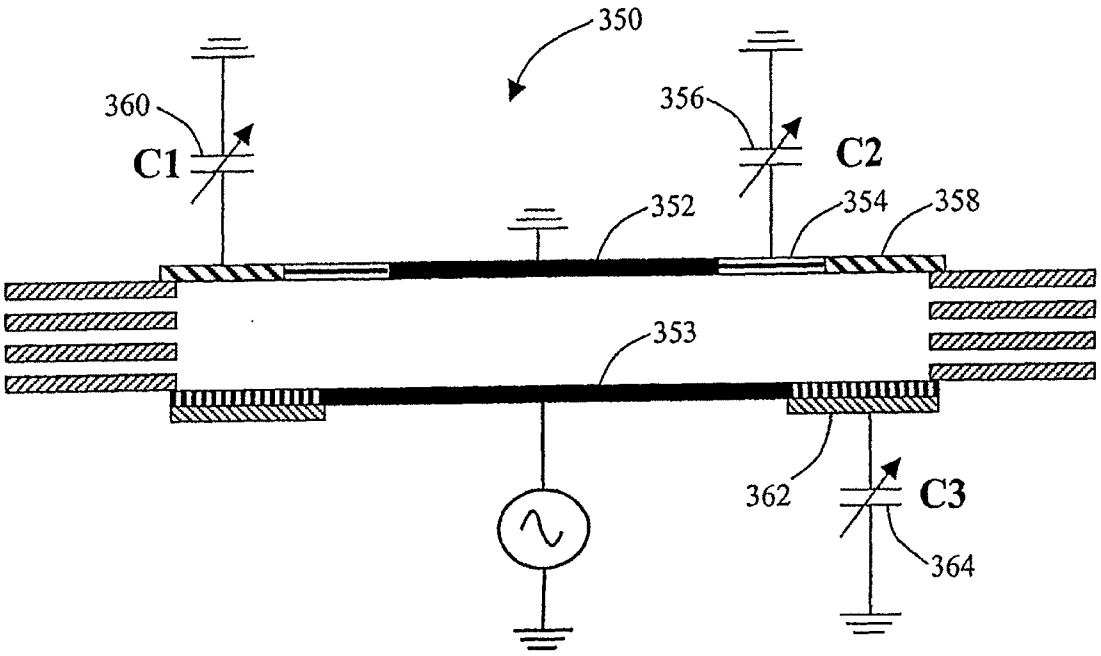

350
360
C1
356
C2
352
354
358
353
362
C3
364

FIG. 6

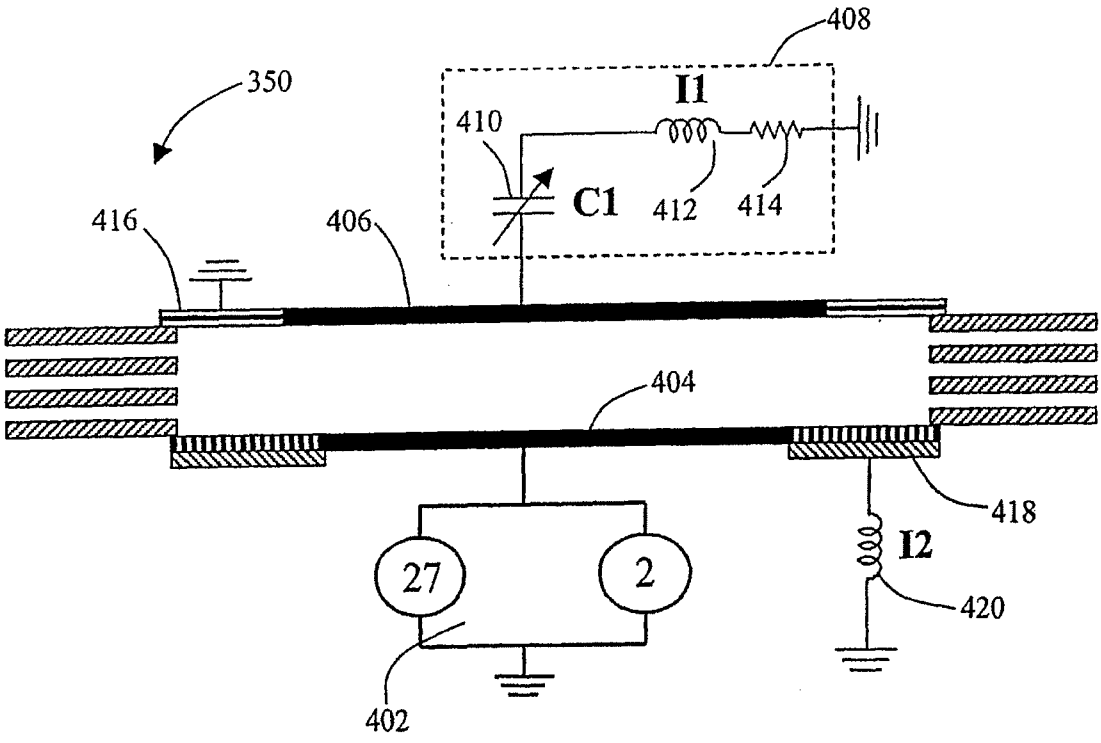

408
350
I1
410
C1
412
414
416
406
404
418
I2
420
27
2
402

FIG. 7

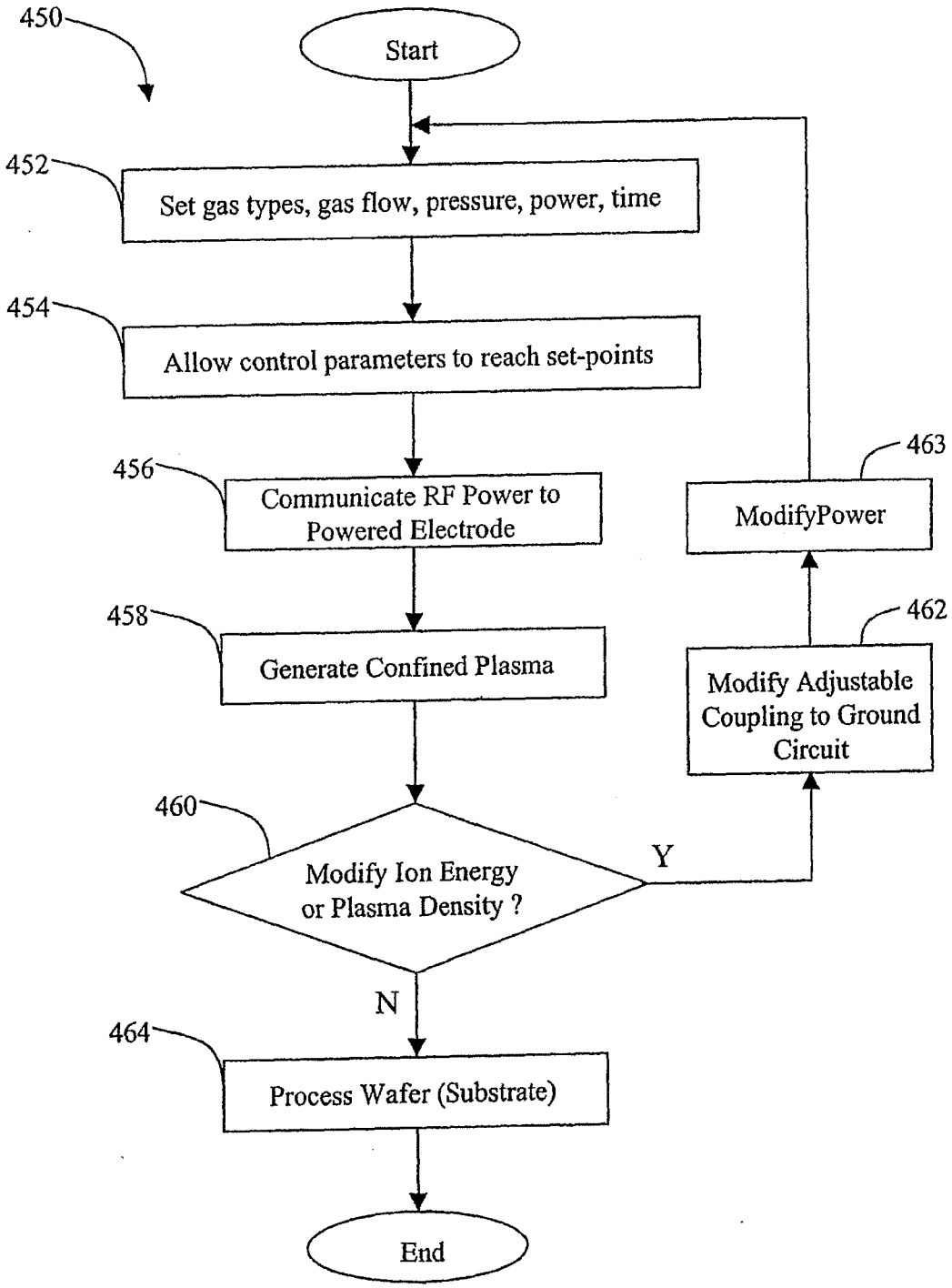

450
Start
452
Set gas types, gas flow, pressure, power, time
454
Allow control parameters to reach set-points
456
Communicate RF Power to Powered Electrode
458
Generate Confined Plasma
460
Modify Ion Energy or Plasma Density ?
Y
N
462
Modify Adjustable Coupling to Ground Circuit
463
ModifyPower
464
Process Wafer (Substrate)
End

FIG. 8